

To our customers,

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## Old Company Name in Catalogs and Other Documents

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April 1<sup>st</sup>, 2010  
Renesas Electronics Corporation

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**P-CHANNEL MOS FIELD EFFECT TRANSISTOR  
FOR SWITCHING**

**DESCRIPTION**

The μPA1830 is a switching device which can be driven directly by a 4.0 V power source.

This device features a low on-state resistance and excellent switching characteristics, and is suitable for applications such as power management of notebook computers and so on.

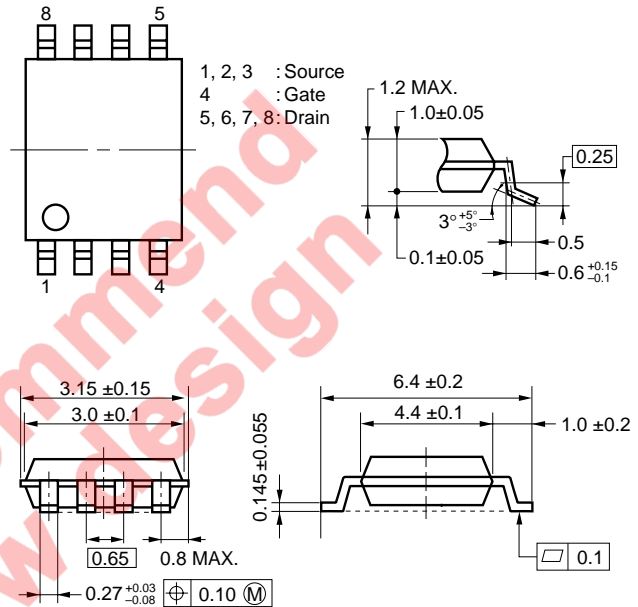
**FEATURES**

- 4.0 V drive available
- Low on-state resistance  
 $R_{DS(on)1} = 17 \text{ m}\Omega \text{ MAX. (} V_{GS} = -10 \text{ V, } I_D = -4.5 \text{ A)}$   
 $R_{DS(on)2} = 24.5 \text{ m}\Omega \text{ MAX. (} V_{GS} = -4.5 \text{ V, } I_D = -4.5 \text{ A)}$   
 $R_{DS(on)3} = 28 \text{ m}\Omega \text{ MAX. (} V_{GS} = -4.0 \text{ V, } I_D = -4.5 \text{ A)}$
- Built-in G-S protection diode against ESD

**ORDERING INFORMATION**

PART NUMBER	PACKAGE
μPA1830GR-9JG	Power TSSOP8

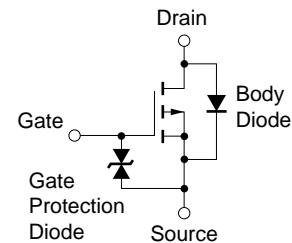
**PACKAGE DRAWING (Unit: mm)**



**ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub> = 25°C)**

Drain to Source Voltage (V <sub>GS</sub> = 0 V)	V <sub>DSS</sub>	-30	V
Gate to Source Voltage (V <sub>DS</sub> = 0 V)	V <sub>GSS</sub>	±20	V
Drain Current (DC) (T <sub>A</sub> = 25°C)	I <sub>D(DC)</sub>	±9.0	A
Drain Current (pulse) <sup>Note1</sup>	I <sub>D(pulse)</sub>	±36	A
Total Power Dissipation <sup>Note2</sup>	P <sub>T</sub>	2.0	W
Channel Temperature	T <sub>ch</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C

**EQUIVALENT CIRCUIT**



**Notes 1.** PW ≤ 10 μs, Duty Cycle ≤ 1%

**2.** Mounted on ceramic substrate of 5000 mm<sup>2</sup> x 1.1 mm

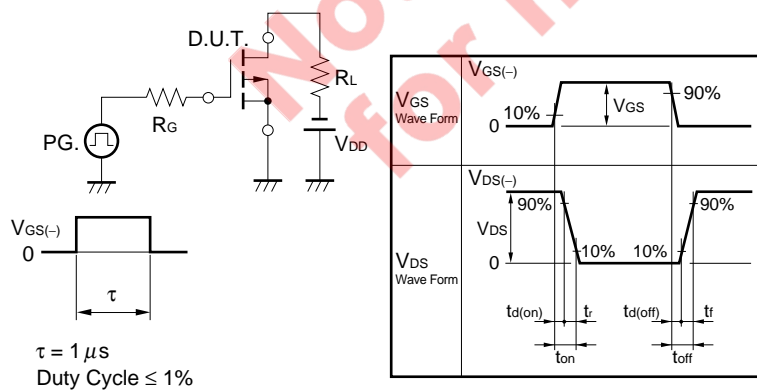
**Remark** The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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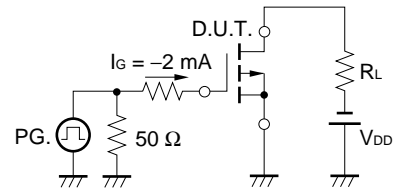
**ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C)**

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = -30 V, V <sub>GS</sub> = 0 V			-1.0	μA
Gate Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20 V, V <sub>DS</sub> = 0 V			±10	μA
Gate Cut-off Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -1.0 mA	-1.0	-2.0	-2.5	V
Forward Transfer Admittance	y <sub>fs</sub>	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -4.5 A	8.0	17.4		S
Drain to Source On-state Resistance	R <sub>DS(on)1</sub>	V <sub>GS</sub> = -10 V, I <sub>D</sub> = -4.5 A		13.7	17	mΩ
	R <sub>DS(on)2</sub>	V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -4.5 A		18.5	24.5	mΩ
	R <sub>DS(on)3</sub>	V <sub>GS</sub> = -4.0 V, I <sub>D</sub> = -4.5 A		21	28	mΩ
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -10 V		1950		pF
Output Capacitance	C <sub>oss</sub>	V <sub>GS</sub> = 0 V		570		pF
Reverse Transfer Capacitance	C <sub>rss</sub>	f = 1.0 MHz		350		pF
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = -15 V, I <sub>D</sub> = -4.5 A		17		ns
Rise Time	t <sub>r</sub>	V <sub>GS</sub> = -10 V		16		ns
Turn-off Delay Time	t <sub>d(off)</sub>	R <sub>G</sub> = 10 Ω		140		ns
Fall Time	t <sub>f</sub>			150		ns
Total Gate Charge	Q <sub>G</sub>	V <sub>DD</sub> = -24 V		38		nC
Gate to Source Charge	Q <sub>GS</sub>	V <sub>GS</sub> = -10 V		4.5		nC
Gate to Drain Charge	Q <sub>GD</sub>	I <sub>D</sub> = -9.0 A		12		nC
Body Diode Forward Voltage	V <sub>F(S-D)</sub>	I <sub>F</sub> = 9.0 A, V <sub>GS</sub> = 0 V		0.84		V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 9.0 A, V <sub>GS</sub> = 0 V		60		ns
Reverse Recovery Charge	Q <sub>rr</sub>	di/dt = 100 A/μs		40		nC

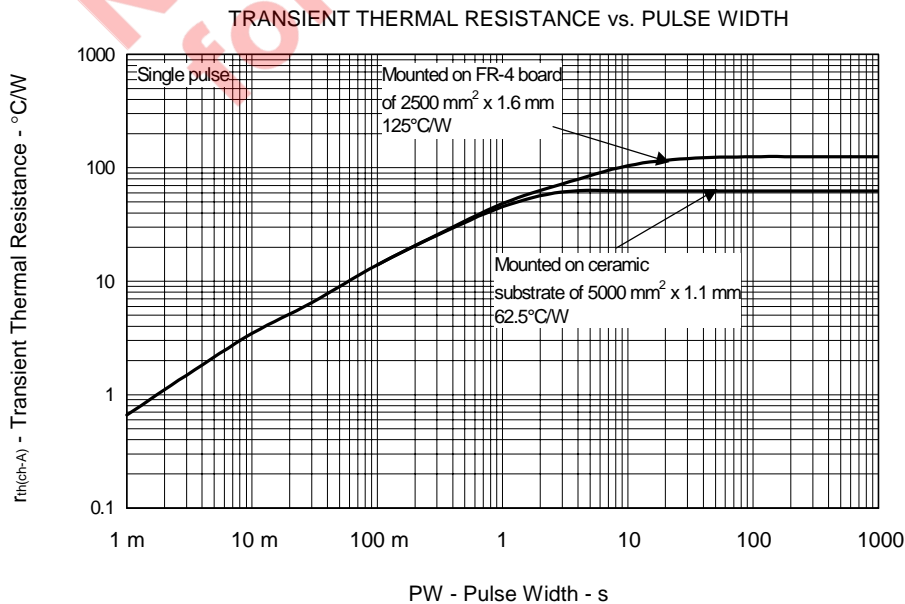
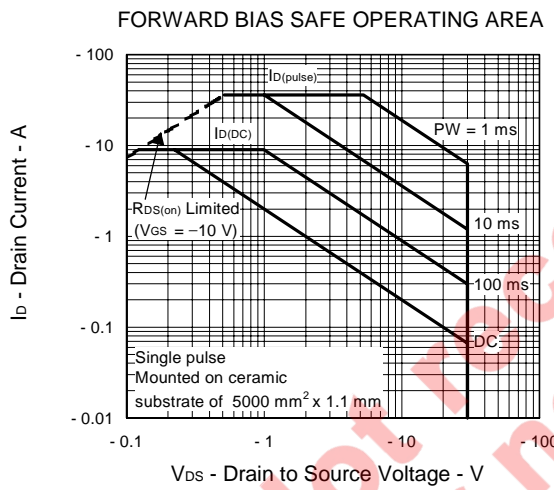
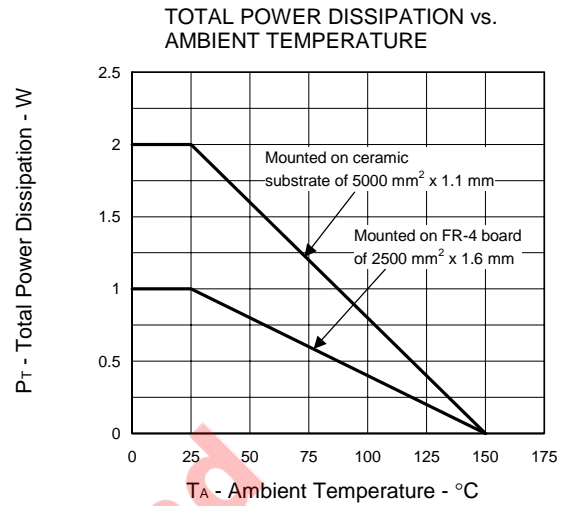
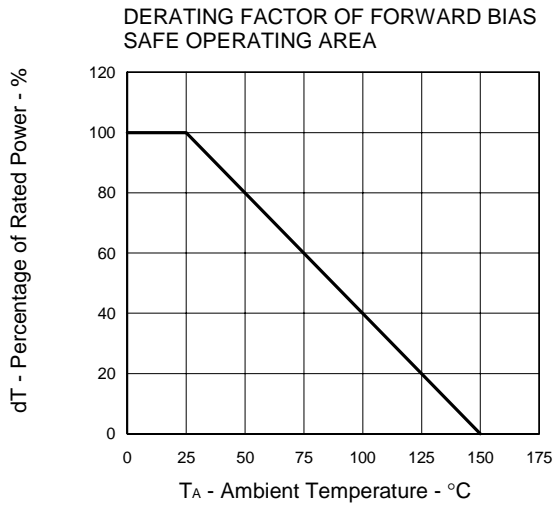
**TEST CIRCUIT 1 SWITCHING TIME**



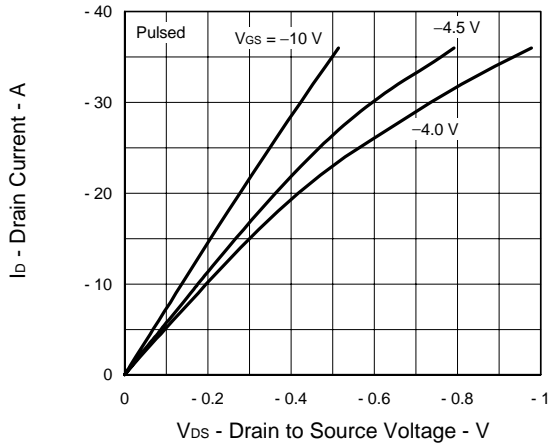
**TEST CIRCUIT 2 GATE CHARGE**



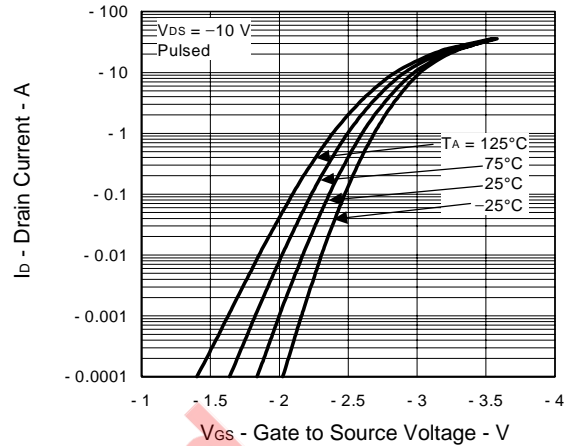
TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25°C)



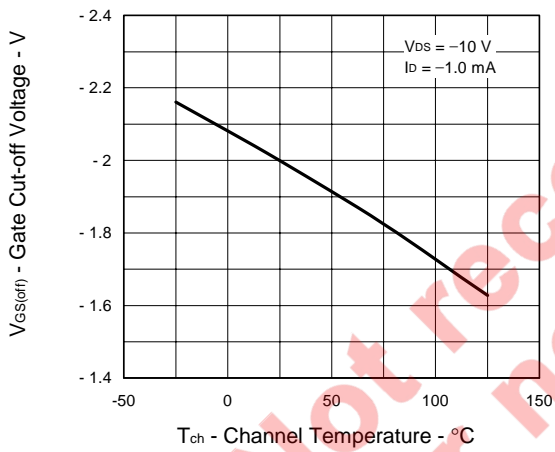
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



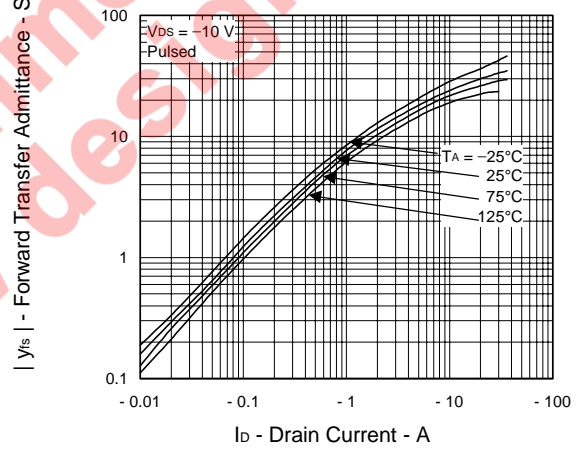
FORWARD TRANSFER CHARACTERISTICS



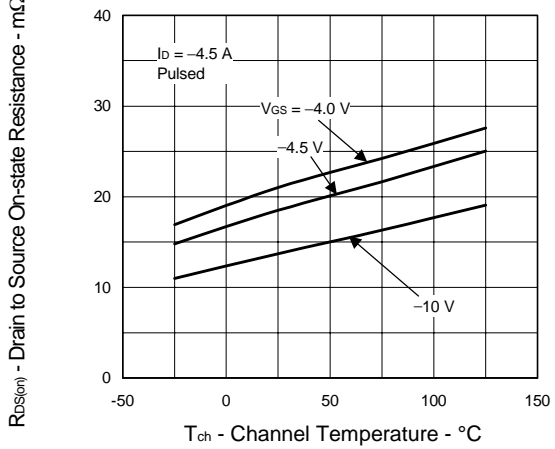
GATE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



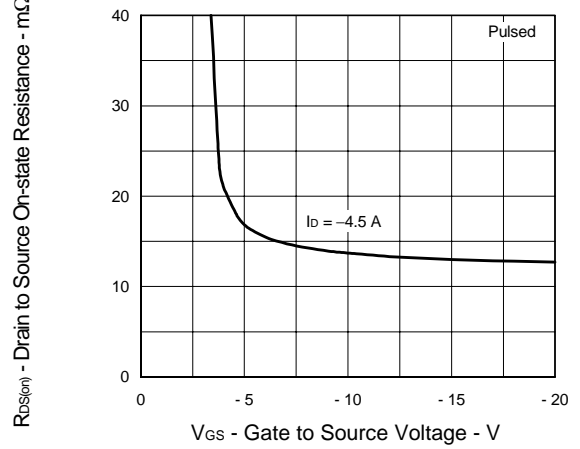
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



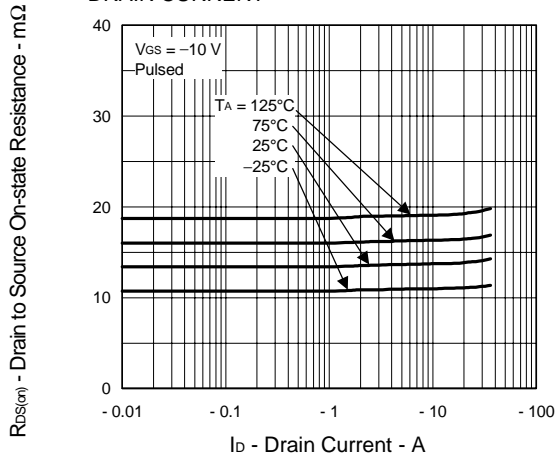
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



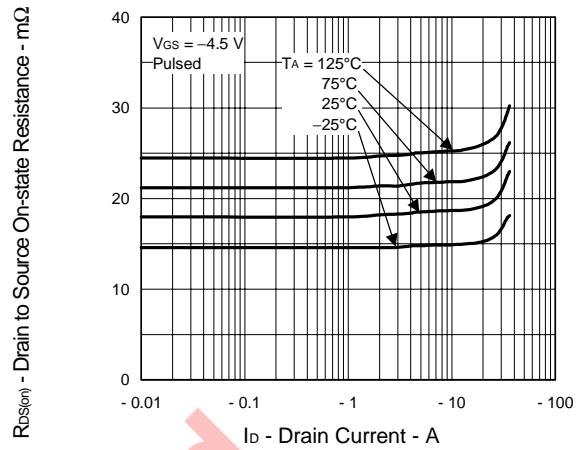
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



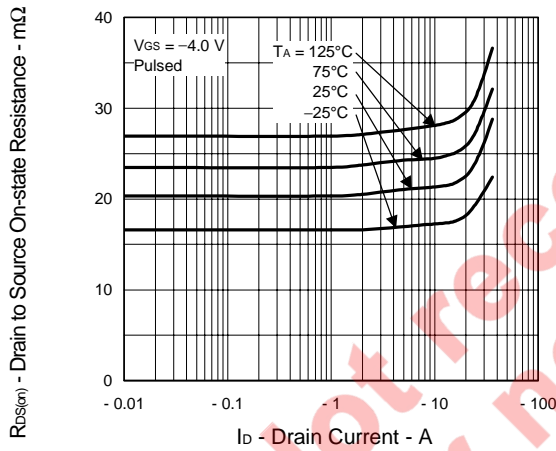
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



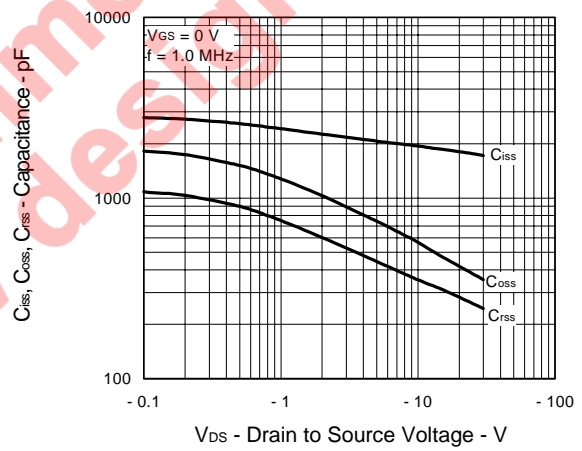
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



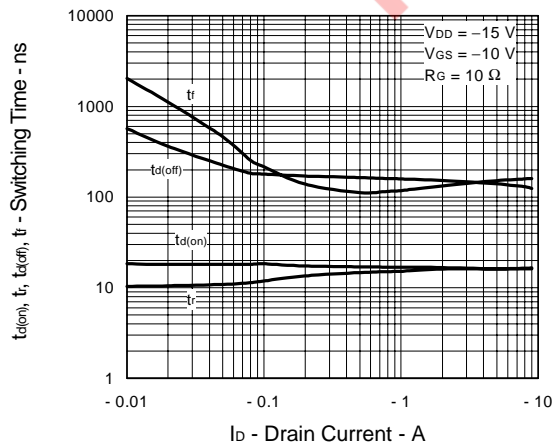
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



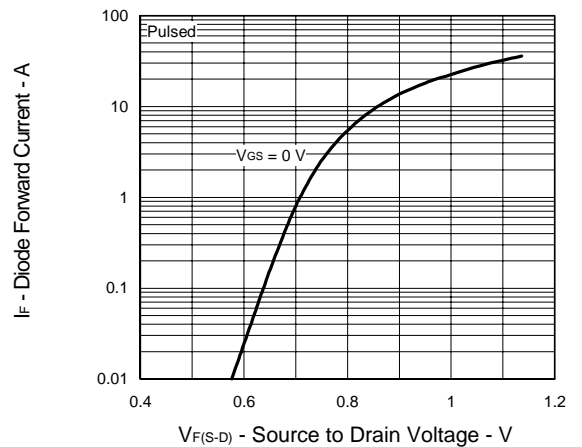
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE

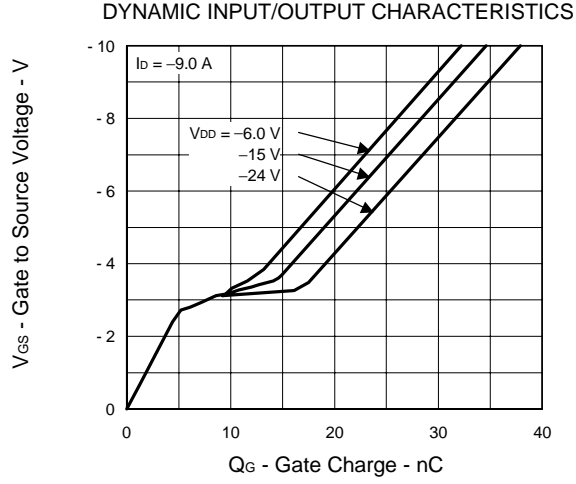


SWITCHING CHARACTERISTICS



SOURCE TO DRAIN DIODE FORWARD VOLTAGE





Not recommend  
for new design



[MEMO]

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